FH32P03G6

P-Channel MOSFET

General Description

The FH32P03G6 is the highest performance trench P-ch MOSFETs with extreme high cell density , which provide excellent RDSON and gate charge for most of the synchronous buck converter applications .

The FH32P03G6 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

Applications

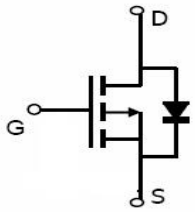
- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

General Features

- V_{DS} = -30V ,I_D =-32A

  $R_{DS(ON)}$ (Typ) 9 m Ω@ V_{GS}= -10V

  $R_{DS(ON)}$ (Typ) 14 mΩ@ V_{GS} = - 4.5V
- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available



Schematic diagram

Marking and Pin Assignment

PDFN3.3x3.3-8L top view

Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous (Note 1)	I_D	-32	A
Drain Current-Continuous(T_C=100℃)	I_D (100℃)	-15	A
Drain Current-Pulsed (Note 1/3)	I_{DM}	-85	A
Maximum Power Dissipation	P_D	29	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Case (Note 2)	$R_{\theta JC}$	3.43	℃/W

Electrical Characteristics (T_A=25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-30V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.1	-1.5	-1.9	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-15A	-	9	14	mΩ
		V_{GS}=-4.5V, I_D=-10A	-	14	19	mΩ
Gate resistance	R_G		-	5.4	-	Ω
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-15A	16	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-25V,V_{GS}=0V, F=1.0MHz	-	1870	-	PF
Output Capacitance	C_{oss}		-	309	-	PF
Reverse Transfer Capacitance	C_{rss}		-	228	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-15V, ID=-15A, V_{GS}=-10V,R_{GEN}=1Ω	-	13	-	nS
Turn-on Rise Time	t_r		-	10	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	27	-	nS
Turn-Off Fall Time	t_f		-	13	-	nS
Total Gate Charge	Q_g	V_{DS}=-15V,I_D=-20A,V_{GS}=-10V	-	47.6	-	nC
Gate-Source Charge	Q_{gs}		-	4.6	-	nC
Gate-Drain Charge	Q_{gd}		-	11.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-20A	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

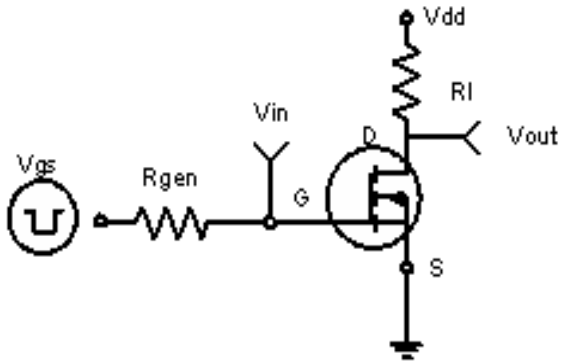


Figure 1:Switching Test Circuit

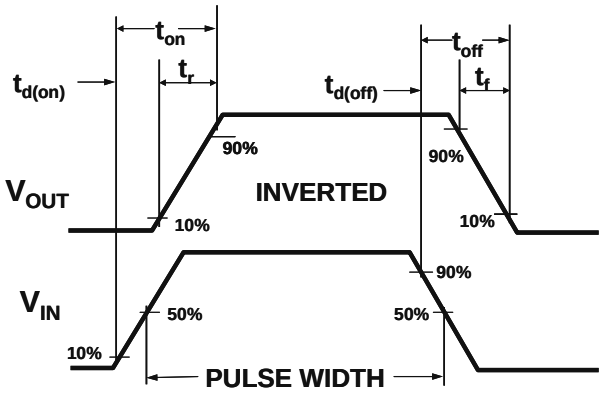


Figure 2:Switching Waveforms

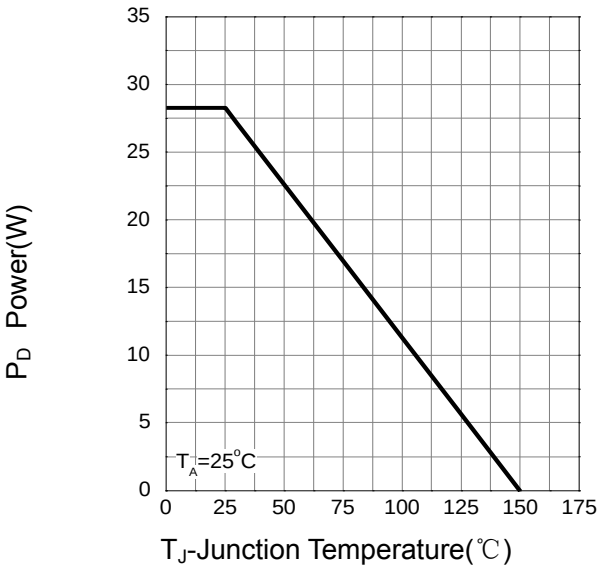


Figure 3 Power Dissipation

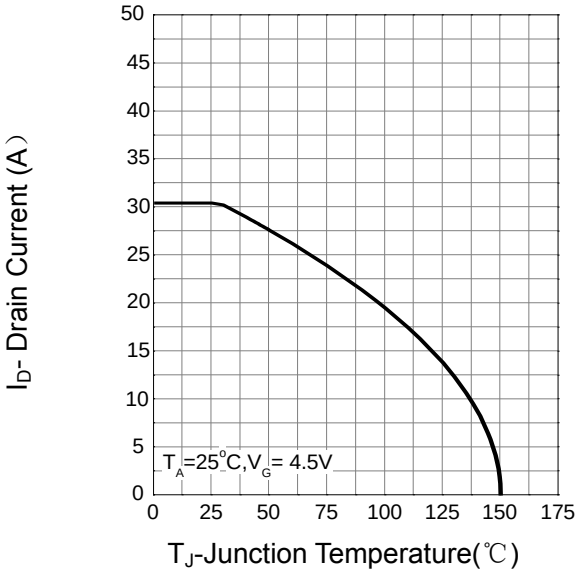


Figure 4 Drain Current

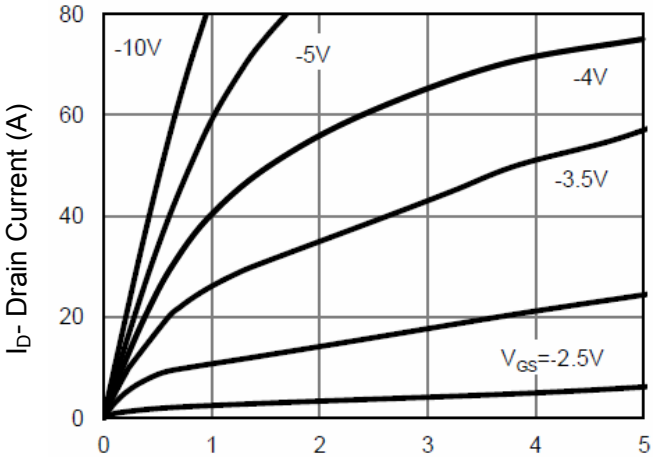


Figure 5 Output Characteristics

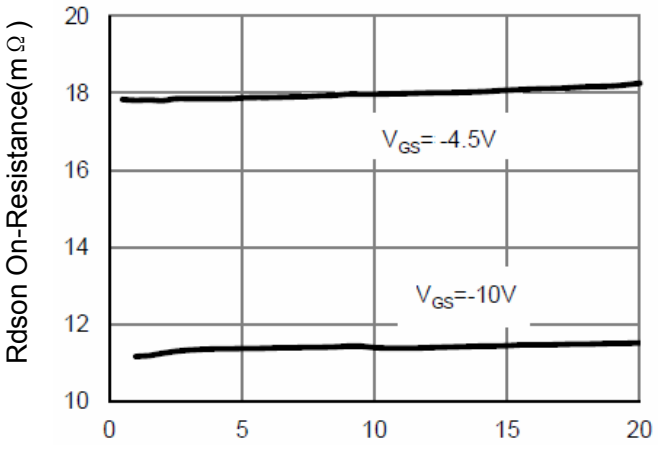


Figure 6 Drain-Source On-Resistance

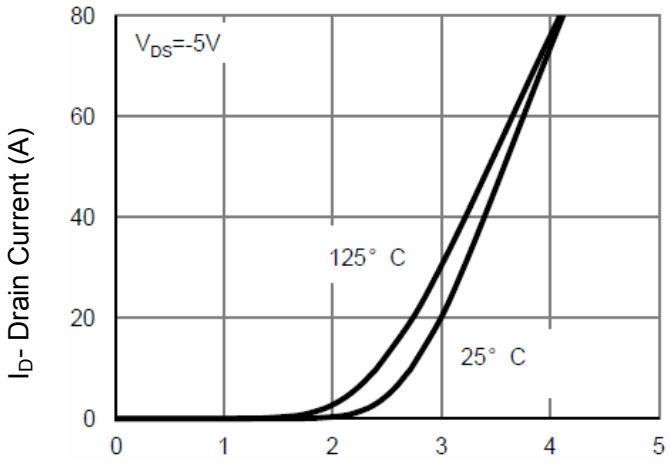


Figure 7 Transfer Characteristics

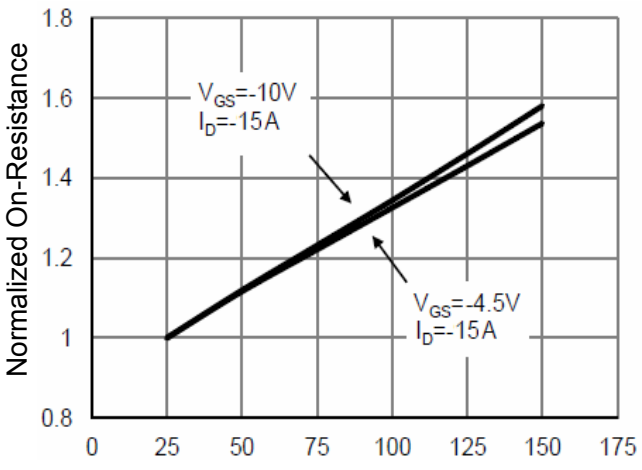


Figure 8 Drain-Source On-Resistance

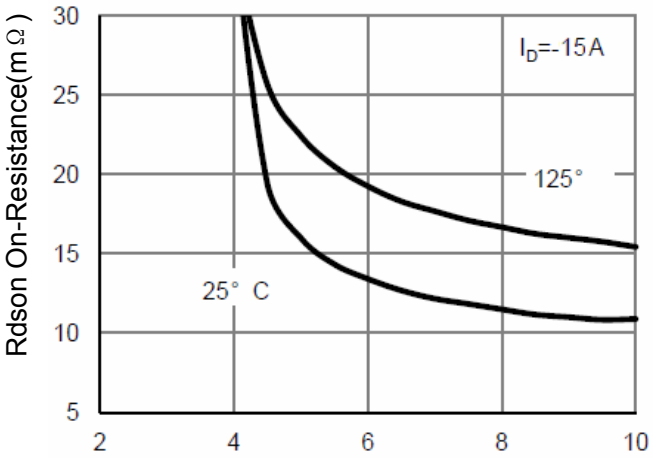


Figure 9 Rdson vs Vgs

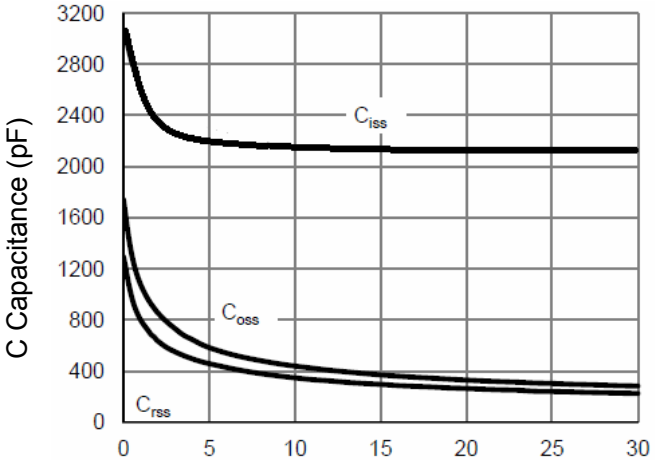


Figure 10 Capacitance vs Vds

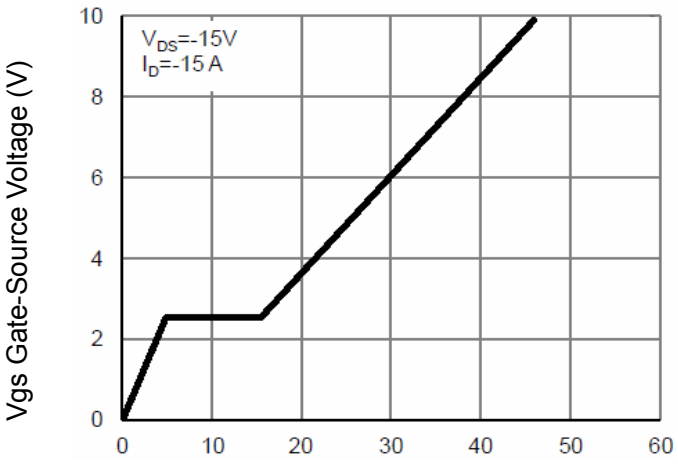


Figure 11 Gate Charge

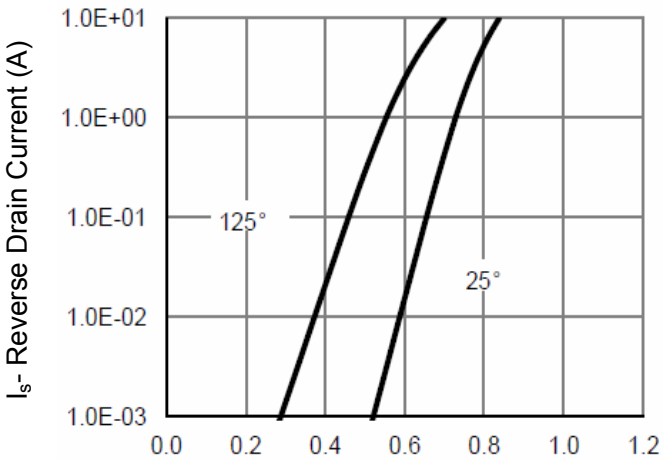
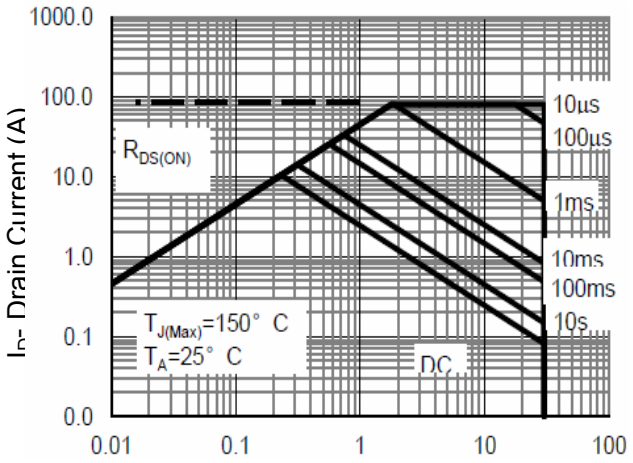
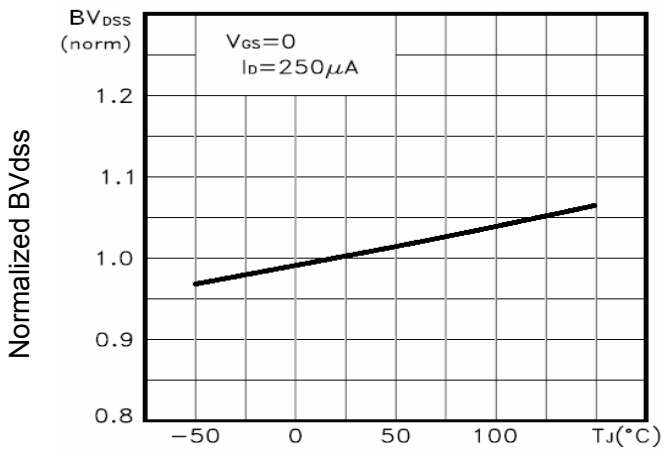


Figure 12 Source- Drain Diode Forward



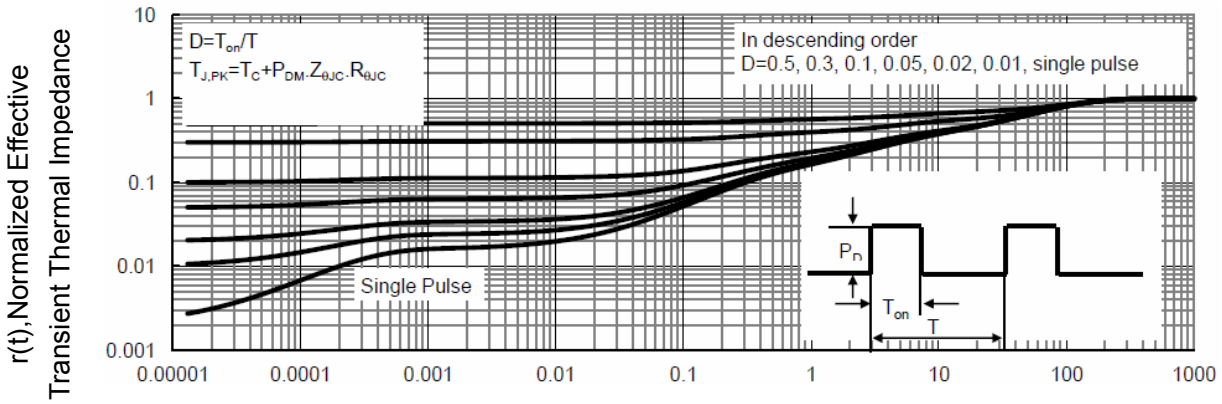
Vds Drain-Source Voltage (V)

Figure 13 Safe Operation Area



T_J-Junction Temperature(℃)

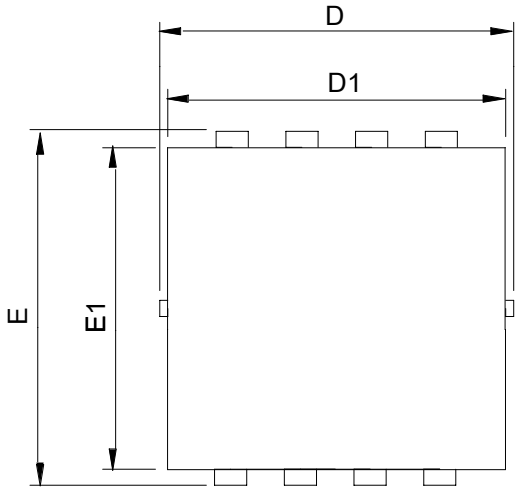
Figure 14 BV_{DSS} vs Junction Temperature



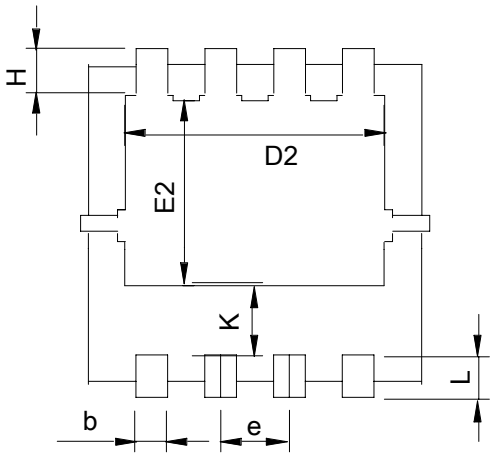
Square Wave Pluse Duration(sec)

Figure 15 Normalized Maximum Transient Thermal Impedance

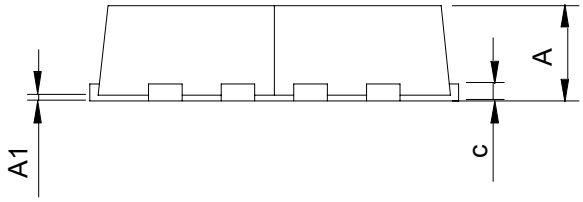
Package Information : PDFN3.3x3.3-8L



Top View



Bottom View



SYMBOL	PDFN3.3x3.3-8L			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022